

Dated 11-July-2019

Tender Notification for Gallium Oxide Wafer

Last Date for submission of tenders: 18:00hrs July 22, 2019

Seeking quotations for epitaxial Ga₂O₃ wafers for high breakdown diodes on DAP Bangalore basis. Quotations should clearly indicate the terms of delivery, delivery schedule, warranty, payment terms, etc. and should reach the undersigned, duly signed on or before 18:00 hours July 22, 2019. The quote should be valid for 30 days. Note: GST is to be charged at 5%. GST concession certificate will be provided. For any questions or clarifications, please contact Dr. Sushobhan Avasthi (savasthi@iisc.ac.in).

Preamble and scope of the purchase

We plan to use epitaxial Ga₂O₃ wafer for making high breakdown voltage heterojunction devices for academic purpose. The scope of the tender is Ga₂O₃ epitaxial field region that can withstand > 2000V (desired) deposited on a highly doped Ga₂O₃ substrate for good Ohmic contacts.

Technical specifications of the Ga₂O₃ epitaxial wafer

Substrate doping (Si or Sn)	> 5e18 cm ⁻³ (as high as possible)
Substrate Orientation	(001)
Substrate thickness	> 300 μm
Epitaxial layer thickness	10 μm
Epitaxial layer doping (Si or Sn)	3e16 cm ⁻³
Wafer size	2 inch diameter
Dicing status	Pre-diced in standard size. 15 mm pitch is preferable



Yours Sincerely,
Dr. Sushobhan Avasthi
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